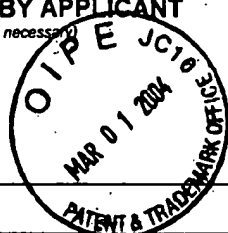


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Application Number	10/612793
Filing Date	July 2, 2003
First Named Inventor	Bhattacharyya, Arup
Group Art Unit	2811
Examiner Name	Unknown

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Attorney Docket No: 1303.111US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
PG	US-2003/0042534	03/06/2003	Bhattacharyya, Arup, et al.	257	317	08/30/2001
	US-2003/0072126	04/17/2003	Bhattacharyya, Arup	361	311	08/30/2001
	US-2003/0089942	05/15/2003	Bhattacharyya, Arup	257	310	11/09/2001
	US-2003/0151948	08/14/2003	Bhattacharyya, Arup, et al.	365	185.18	02/12/2002
	US-2003/0160277	08/28/2003	Bhattacharyya, Arup, et al.	257	503	02/27/2003
	US-2004/0014304	01/22/2004	Bhattacharyya, Arup	438	570	07/18/2002
	US-3,918,033	11/04/1975	Case, Jerry R., et al.	365	180	11/11/1974
	US-3,964,085	06/15/1976	Kahng, Duwon, et al.	428	428	08/18/1975
	US-3,978,577	09/07/1976	Bhattacharyya, Arup, et al.	29	571	06/30/1975
	US-4,488,262	12/01/1984	Basire, Dominique, et al.	365	104	06/17/1982
	US-4,791,604	12/13/1988	Lienau, Richard M., et al.	365	9	07/23/1986
	US-4,829,482	05/09/1989	Owen	365	189.09	10/18/1985
	US-4,870,470	09/26/1989	Bass Jr., Roy S., et al.	357	23.5	10/16/1987
	US-5,043,946	08/27/1991	Yamauchi, Y., et al.	365	185.08	03/07/1990
	US-5,396,454	03/07/1995	Nowak, Edward D.	365	154	09/24/1993
	US-5,621,683	04/15/1997	Young, Nigel D.	365	185.05	12/05/1995
	US-5,627,779	05/06/1997	Odake, Yoshinori, et al.	365	185.01	07/21/1995
	US-5,801,993	09/01/1998	Choi, Woong L.	365	185.28	08/07/1997
	US-5,814,853	09/29/1998	Chen, Jian	257	315	01/22/1996
	US-5,963,476	10/05/1999	Hung, C., et al.	365	185.22	11/12/1997
	US-5,981,335	11/09/1999	Chi, Min-Hwa	438	253	11/20/1997
	US-6,104,045	08/15/2000	Forbes, Leonard, et al.	257	141	05/13/1998
	US-6,201,734	03/13/2001	Sansbury, J. D., et al.	365	185.1	09/25/1998
	US-6,243,296	06/05/2001	Sansbury, James D.	365	185.18	06/22/1999
	US-6,294,427	09/25/2001	Furuhata, Tomoyuki, et al.	438	257	05/02/2000
	US-6,462,359	10/08/2002	Nemati, Farid, et al.	257	107	03/22/2001
	US-6,545,297	04/08/2003	Noble, Wendell P., et al.	257	124	05/13/1998
	US-6,574,143	06/03/2003	Nakazato, Kazuo	365	185.18	12/08/2000
	US-6,653,174	11/25/2003	Cho, Hyun-Jin, et al.	438	133	12/17/2001
	US-6,653,175	11/25/2003	Nemati, Farid, et al.	438	133	08/28/2002

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
PG	JP-61-166078	07/26/1986	Ariga, R.	H01L	29/78	

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Application Number	10/612793
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First Named Inventor	Bhattacharyya, Arup
Group Art Unit	2811
Examiner Name	Unknown

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
Re		BAUER, F, et al., "Design aspects of MOS controlled thyristor elements", <u>International Electron Devices Meeting 1989. Technical Digest</u> , (1989), 297-300	
		BHATTACHARYYA, A., "Physical & Electrical Characteristics of LPCVD Silicon Rich Nitride", <u>ECS Technical Digest, J. Electrochem. Soc.</u> , 131(11), 691 RDP, New Orleans, (1984), 469C	
		CARTER, R J., "Electrical Characterization of High-k Materials Prepared By Atomic Layer CVD", <u>IWGI</u> , (2001), 94-99	
		CHANG, H R., et al., "MOS trench gate field-controlled thyristor", <u>Technical Digest - International Electron Devices Meeting</u> , (1989), 293-296	
		CHOI, J D., et al., "A0.15 um NAND Flash Technology with .11 um ² cell Size for 1 Gbit Flash Memory", <u>IEDM Technical Digest</u> , (2000), 767-770	
		FROHMAN-BENTCHKOWSKY, D., "An integrated metal-nitride-oxide-silicon (MNOS) memory", <u>Proceedings of the IEEE</u> , 57(6), (June 1969), 1190-1192	
		HAN, KWANGSEOK, "Characteristics of P-Channel Si Nano-Crystal Memory", <u>IEDM Technical Digest, International Electron Devices Meeting</u> , (December 10-13, 2000), 309-312	
		JAGAR, S., "Single grain thin-film-transistor (TFT) with SOI CMOS performance formed by metal-induced-lateral-crystallization", <u>International Electron Devices Meeting 1999. Technical Digest</u> , (1999), 293-6	
		KUMAR, M. J., "Lateral Schottky Rectifiers for Power Integrated Circuits", <u>International Workshop on the Physics of Semiconductor Devices</u> , 11th, 4746, Allied Publishers Ltd., New Delhi, India, (2002), 414-421	
		LAI, S K., et al., "Comparison and trends in Today's dominant E2 Technologies", <u>IEDM Technical Digest</u> , (1986), 580-583	
		NEMATI, F, et al., "A novel high density, low voltage SRAM cell with a vertical NDR device", <u>1998 Symposium on VLSI Technology Digest of Technical Papers</u> , (1998), 66-7	
		NEMATI, F, et al., "A novel thyristor-based SRAM cell (T-RAM) for high-speed, low-voltage, giga-scale memories", <u>International Electron Devices Meeting 1999. Technical Digest</u> , (1999), 283-6	
		OHSAWA, T., "Memory design using one-transistor gain cell on SOI", <u>IEEE International Solid-State Circuits Conference. Digest of Technical Papers</u> , vol. 1, (2002), 152-455	
		OKHONIN, S., "A SOI capacitor-less 1T-DRAM concept", <u>2001 IEEE International SOI Conference. Proceedings, IEEE</u> , 2001, (2000), 153-4	
		SHINOHE, T, et al., "Ultra-high di/dt 2500 V MOS assisted gate-triggered thyristors (MAGTs) for high repetition excimer laser system", <u>International Electron Devices Meeting 1989. Technical Digest</u> , (1989), 301-4	
		SZE, S. M., "Table 3: Measured Schottky Barrier Heights", <u>In: Physics of Semiconductor Devices</u> , John Wiley & Sons, Inc., (1981), pg. 291	
		TIWARI, SANDIP, "Volatile and Non-Volatile Memories in Silicon with Nano-Crystal Storage", <u>Int'l Electron Devices Meeting: Technical Digest</u> , Washington, DC, (Dec. 1995), 521-524	
		VAN MEER, H., "Ultra-thin film fully-depleted SOI CMOS with raised G/S/D device architecture for sub-100 nm applications", <u>2001 IEEE International SOI Conference</u> , (2001), 45-6	
		ZHANG, H., "Atomic Layer Deposition of High Dielectric Constant Nanolaminates", <u>Journal of The Electrochemical Society</u> , 148(4), (April 2001), F63-F66	

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	Application Number	10/612793
	Filing Date	July 2, 2003
	First Named Inventor	Bhattacharyya, Arup
	Group Art Unit	2826
	Examiner Name	Erdem, Fazli
Sheet 1 of 1	Attorney Docket No: 1303.111US1	

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
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Re		FAZAN, P, et al., "Capacitor-Less 1-Transistor DRAM", <u>IEEE International SOI Conference</u> , (2002), 10-13	

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May 31, 04

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